Bipolar Transistor

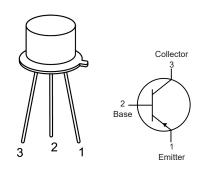
multicomp PRO



Maximum Ratings

Characteristic	Symbol	Rating	Unit		
Collector - Base Voltage	Vсво	80	V		
Collector - Emitter Voltage	VCEO	60	V		
Emitter - Base Voltage	Vево	6	А		
Base Current	lв	500	mA		
Collector Current Continuous	Ic	1	А		
Power Dissipation @ Ta = 25°C Derate Above 25°C	Pb	1 5.3	W mW/°C		
Power Dissipation @ Tc = 25°C Derate Above 25°C	Pb	6 34	W mW/°C		
Operating and Storage Junction Temperature Range	ТЈ, Тѕтс	-65 to +200	°C		
Thermal Characteristics					
Junction to Case	Rth(jc)	29	°C/W		

RoHS Compliant



Electrical Characteristics: (T_A = +25°C Unless otherwise specified)

Parameter	Symbol	Test Conditions	Value	Unit
Collector Emitter Voltage	VCEO	Ic = 1mA, 1 _B = 0	60	V
Collector Cut Off Current	ICEX	VCE = 50V, VEB = 1.5V VCE = 80V, VEB = 1.5V VCE = 100V, VEB = 1.5V TC = 150°C	0.1	mA
		VCE = 30V, VEB = 1.5V VCE = 50V, VEB = 1.5V VCE = 70V, VEB = 1.5V	1	mA

Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Collector Cut Off Current	Ісво	Vcв=Rated Vcво, IE=0	-	-	0.1	
Collector Cut Off Current	ICEO	Vcв=Rated Vcво, IE=0	-	-	0.07	mA
Emitter Cut Off Current	ІЕВО	VEB = 6V, IC = 0	-	-	0.5	
DC Current Gain	*hFE	Ic = 50mA, VcE = 1V Ic = 250mA, VcE = 1V Ic = 500mA, VcE = 1V Ic = 1A, VcE = 1V	30 30 30 15	-	150	

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Bipolar Transistor



Small Signal Characteristics

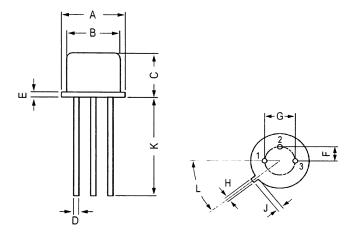
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Small Signal Characteristics	*VCE (sat)	Ic = 500mA, Iв = 50mA Ic = 1A, Iв = 0.1A	-	-	0.3 0.6	.,
Base Emitter Saturation Voltage	*VBE (sat)	Ic = 1A, IB = 0.1A	-	-	1.5	V
Base Emitter On Voltage	*VBE (on)	Ic = 250mA, VcE = 1V	-	-	1	

Small Signal Characteristics

Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Output Capacitance	Cobo	Vсв = 10V, IE = 0, f = 0.1MHz	-	-	100	pF
Small Signal Current Gain	h _{fe}	lc = 100mA, VcE = 10V, f = 1KHz	30	1	ı	
Current Gain High Frequency	lh _{fe} l	lc = 100mA, VcE = 10V, f = 1MHz	1	-	-	

^{*}Pulse Test: Pulse Width ≤300µS, Duty Cycle ≤2%

TO-39 Metal Can Package



Dim.	Min.	Max.
Α	8.5	9.39
В	7.74	8.5
С	6.09	6.6
D	0.4	0.53
E	-	0.88
F	2.41	2.66
G	4.82	5.33
Н	0.71	0.86
J	0.73	1.02
K	12.7	-
L	42 Deg.	48 Deg.

Part Number Table

Description	Part Number			
Transistor, PNP, 3A, 60V, TO-39	2N4238			

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Dimensions: Millimetres

